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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

SHEET 2 of 2

Complete if Known

Application Number 10/727,705

Filing Date December 3, 2003

First Named Inventor Arlynn W. Smith

Art Unit 2878

Examiner Name

Attorney Docket No. ITDE-PNV114

NON-PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
✓	1	A.W. Smith et al.; "A new texturing geometry for producing high efficiency solar cells with no antireflection coatings", Solar Energy Materials and Solar Cells, Vol. 29, pps. 51-65, 1993	<input type="checkbox"/>
	2	J. Freeman et al., "Hybrid photodiode crosstalk due to backscattered electrons", Nucl. Instr. and Meth. Phys. Res. A (NIMA), Vol. 474, pps. 143-150, 2001	<input type="checkbox"/>
	3	G. Williams Jr. et al., "Electron bombarded back illuminated CCD sensor for low light level imaging applications", Proceedings of SPIE, Vol. 2415, pps. 211-235, 1995	<input type="checkbox"/>
	4	F. Andoh et al., "Development of a novel image intensifier of an amplified metal-oxide-semiconductor imager overlaid with electron bombardment amorphous silicon", IEEE Trans. Elec. Dev., Vol. 45, pps. 778-784, 1998	<input type="checkbox"/>
	5	T.A. Yost et al., "Large area, high speed phototube with a GaAsP photocathode and GaAs metal-semiconductor-metal anode", IEEE, pps. 90-92, 1998	<input type="checkbox"/>
	6	W. van Roosbroeck, "Theory of the yield and Fano factor of electron-hole pairs generated in semiconductors by high-energy particles", Phys. Rev., Vol. 139, pps. A1703-1716, 1965	<input type="checkbox"/>
	7	E.J. Bender, "Present image intensifier tube structures", in Electro-Optical Imaging: System Performance and Modelling, L.M. Biberman, SPIE Press, Bellingham, Washington, 2000	<input type="checkbox"/>
✓	8	A.W. Smith et al., "Ray tracing analysis of the inverted pyramid texturing geometry for high efficiency silicon solar cells," Solar Energy Materials and Solar Cells, Vol. 29, pps. 37-49, 1993	<input type="checkbox"/>
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

¹Applicant's unique citation designation number (optional).

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